

09/473,988

REMARKS

Claims 1-9 and 20 are pending. Claims 2, 4, 7 and 9 have been allowed. Claims 1 and 8 have been amended in order to more particularly point out and distinctly claim the subject matter to which the applicant regards as the invention.

Attached hereto is a marked-up version of the changes made to the claim by the current amendment. The attached page is captioned "Version with markings to show changes made."

Prompt and favorable action on the merits is earnestly solicited.

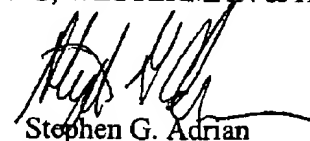
Should the Examiner deem that any further action by applicants would be desirable to place the application in condition for allowance, the Examiner is encouraged to telephone applicants' undersigned attorney.

09/473,988

In the event that any fees are due in connection with this paper, please charge our Deposit  
Account No. 01-2340.

Respectfully submitted,

ARMSTRONG, WESTERMAN & HATTORI, LLP



Stephen G. Adrian  
Attorney for Applicant  
Reg. No. 32,878

SGA/arf

Atty. Docket No. 991493  
Suite 1000  
1725 K Street, N.W.  
Washington, D.C. 20006  
(202) 659-2930



23850

PATENT TRADEMARK OFFICE

Attachment: Version with markings to show changes made

HAHOMENAYNAY9911991493 Prel Amend 06 25 03

**VERSION WITH MARKINGS TO SHOW CHANGES MADE (09/473,988)****IN THE CLAIMS:****Claims 1 and 8 have been amended as follows:**

1. (Five Times Amended) A semiconductor device comprising an insulating interlayer formed on a conductive film, said insulating interlayer including:

- a first insulating layer of a composition containing SiH;
- a second insulating layer formed on said first insulating layer; and
- a third insulating layer formed between said conductive film and said first insulating layer,

wherein said first insulating layer has an H content of not less than 15.4 atom% in the composition after curing, and has been formed to cover said conductive film, and

said second insulating layer has a multilayer structure made up from layers of the same material.

8. (Six Times Amended) A semiconductor device comprising a semiconductor element formed on a semiconductor substrate, and a multilayer interconnection structure formed over said semiconductor element and electrically connected to said semiconductor element,

wherein said multilayered interconnection structure is an interconnection structure of at least two layers in which a conductive film or a lower interconnection layer and an upper interconnection layer formed on an insulating interlayer are electrically connected through a

09/473,988

contact hole formed in said insulating interlayer,

said insulating interlayer includes:

a first insulating layer of a composition containing SiH; and

a second insulating layer formed on said first insulating layer; and

a third insulating layer formed between said conductive film and said first insulating layer,

said first insulating layer has an H content of not less than 15.4 atom% in the composition after curing, and has been formed to cover said conductive film or the lower interconnection layer with the third insulating layer being interposed therebetween, and

said second insulating layer has a multilayer structure made up from layers of the same material.